

Amendments to the Specification:

Please replace the paragraph beginning at page 19, line 18 with the following amended paragraph.

Referring to Fig. 6, an embodiment of a die-to-wafer structure 70 is provided, which includes a first die 72 disposed over and coupled to a second die 76, via a conductive bond film 74a. Optionally, the bond film 74b, e.g., adhesive material, may also be provided to further strengthen the bond formed between the first die 72 and the second die 76, which is provided as part of a larger integrated circuit or wafer 78. The bond films 74a and 74b or segments may be provided as any of the types described above in conjunction with Figs. 1-4 (e.g., conductive interface portion 38 and interface portion 41, respectively) and serves to bond the first die 72 to the second die 76, as described above. Thus, to provide the die-to-wafer structure 70, the bond films 74a, 74b can be first applied to a wafer (not shown) of which the first die 72 is a part. While the first die 72 is part of the wafer, the bond film can be patterned or otherwise disposed on the die 72 using a variety of different techniques, including those techniques described in copending U.S. Patent Application Serial No. 10/655,670 (now U.S. Patent No. 7064055) [\_\_\_\_\_], filed on September 5, 2003, which is entitled METHOD OF FORMING A MULTI-LAYER SEMICONDUCTOR STRUCTURE HAVING A SEAMLESS BONDING INTERFACE, which is commonly assigned to the Assignee of the present application and which is hereby incorporated by reference in its entirety. Once the bond films 74a, 74b are disposed on the wafer including the first die 72, the first die 72 is cut or otherwise separated from the wafer.

Please replace the paragraph beginning at page 20, line 16 with the following amended paragraph.

Once the first die 72 and the second die 76 are properly aligned, at least the first die 72 is exposed to a method for bonding the first and second dies 72, 76, via the bond films 74a, 74b,

which is similar to that described in Fig. 1 of commonly assigned U.S. Patent Application Serial No. 10/655,670, (now U.S. Patent No. 7064055) [ \_\_\_\_\_ ], as described above. The particular temperatures and pressures used for bonding the first and second dies 72, 76 will depend upon a variety of factors, including but not limited to, the specific material from which the bond film 74 is provided, as well as the size, shape and material from which the first die 72 is provided, as well as the size, shape and material from which the second die 76 is provided.